

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Continuous Collector Current	I _C	100	mA
Peak Pulse Collector Current	I _{CM}	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

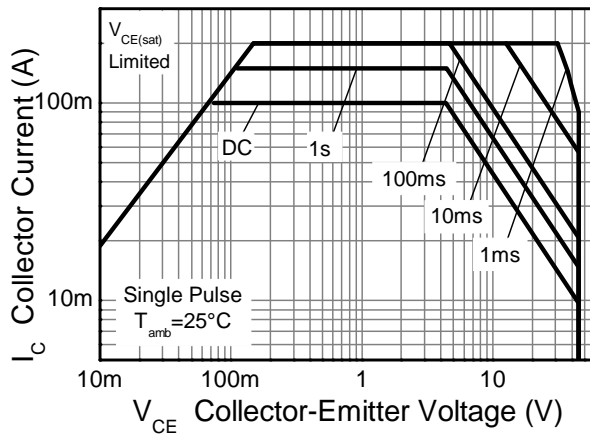
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	435	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	287	°C/W
Thermal Resistance, Junction to Lead (Note 6)	R _{θJL}	150	°C/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

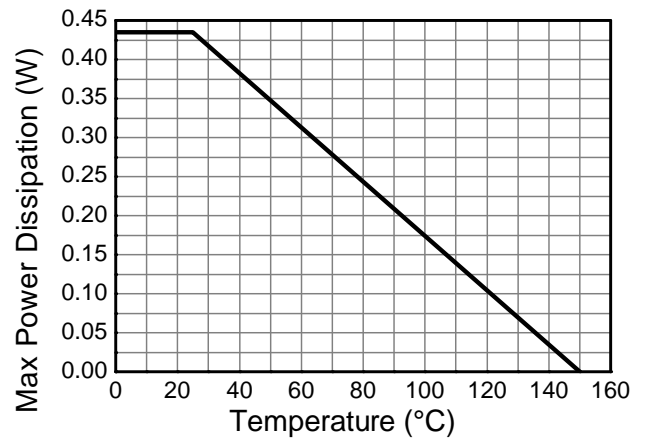
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

- Notes:
- For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
 - Thermal resistance from junction to solder-point (on the exposed collector pad).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

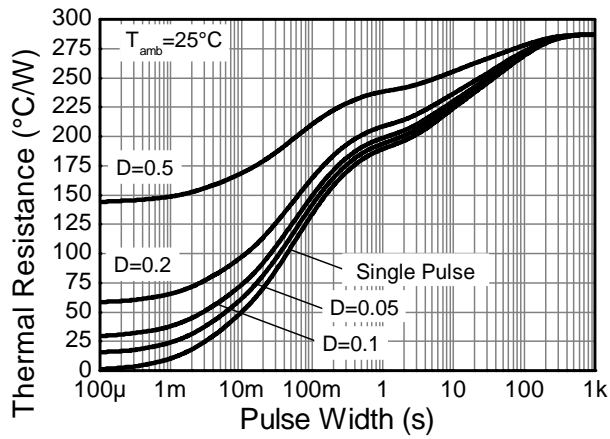
Thermal Characteristics and Derating Information



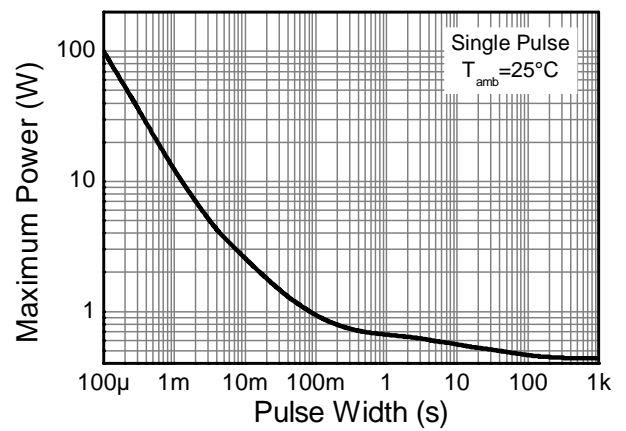
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typical	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	50	150	—	V	I _C = 50μA, I _B = 0
Collector-Emitter Breakdown Voltage	BV _{CES}	50	150	—	V	I _C = 50μA, I _B = 0
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	45	65	—	V	I _C = 1mA, I _B = 0
Collector-Base Breakdown Voltage	BV _{EBO}	6.0	8.35	—	V	I _E = 50μA, I _C = 0
Collector-Base Cut-Off Current	I _{CBO}	—	—	15	nA	V _{CB} = 40V
Collector-Emitter Cut-Off Current	I _{CES}	—	—	15	nA	V _{CE} = 40V
ON CHARACTERISTICS (Note 8)						
DC Current Gain	h _{FE}	— 200	220 260	— 470	—	I _C = 10μA, V _{CE} = 5.0V I _C = 2.0mA, V _{CE} = 5.0V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	50 122	125 300	mV	I _C = 10mA, I _B = 0.5mA I _C = 100mA, I _B = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	760 880	1,000 1,100	mV	I _C = 10mA, I _B = 0.5mA I _C = 100mA, I _B = 5.0mA
Base-Emitter Voltage	V _{BE(on)}	580 —	650 725	750 800	mV	I _C = 2.0mA, V _{CE} = 5V I _C = 10mA, V _{CE} = 5V
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	—	1.5	—	pF	V _{CB} = 10.0V, f = 1.0MHz, I _E = 0
Current Gain-Bandwidth Product	f _T	100	170	—	MHz	V _{CE} = 5V, I _C = 10mA, f = 100MHz

Note: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

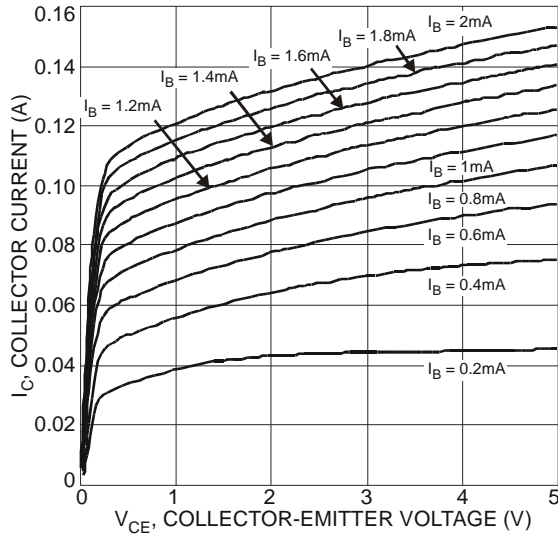


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

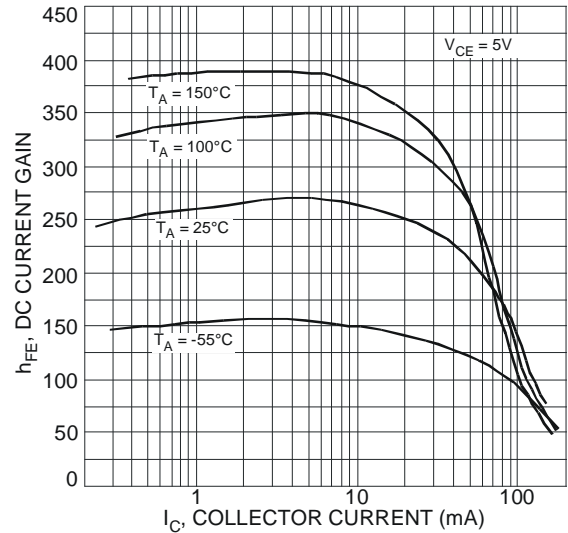


Fig. 5 Typical DC Current Gain vs. Collector Current

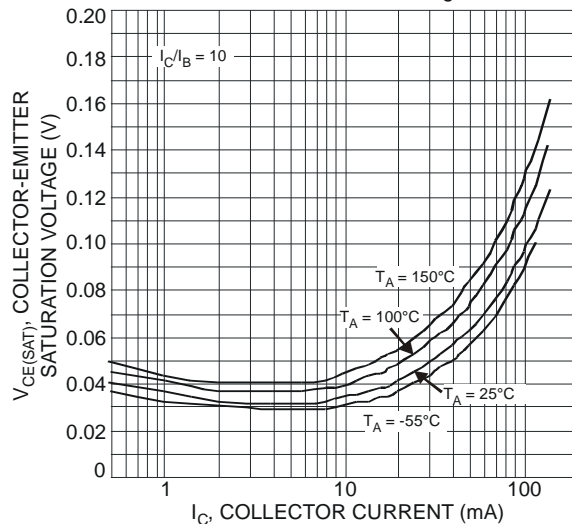


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

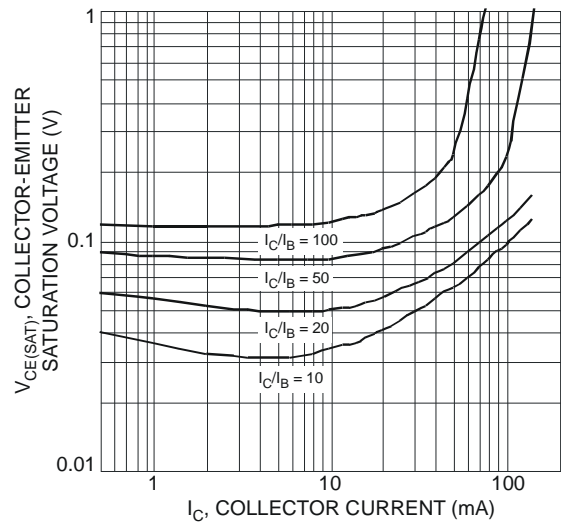


Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current

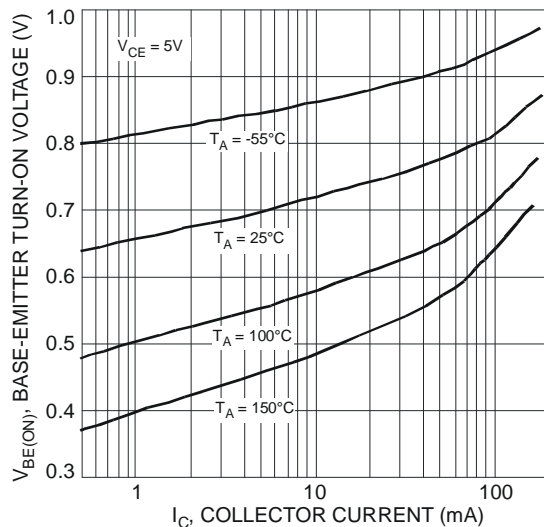


Fig. 8 Typical Base-Emitter Turn-On Voltage vs. Collector Current

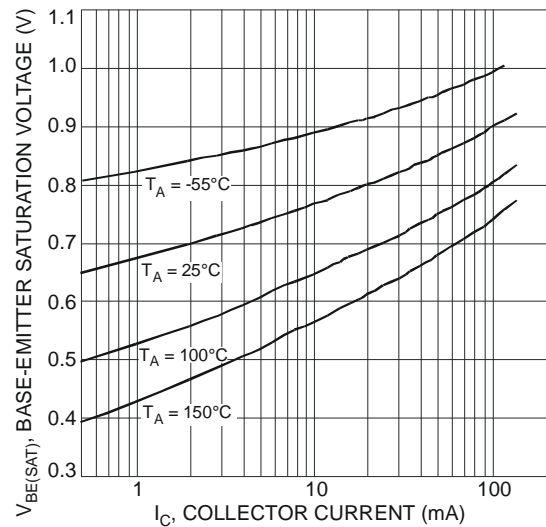
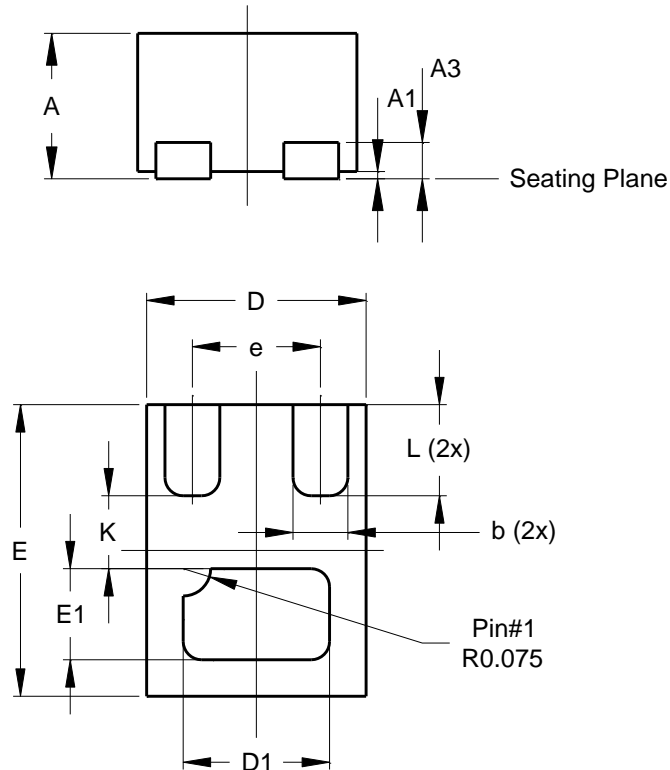


Fig. 9 Typical Base-Emitter Saturation Voltage vs. Collector Current

Package Outline Dimensions

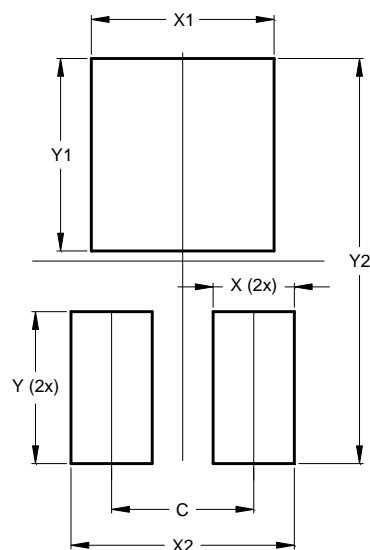
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



X2-DFN0806-3			
Dim	Min	Max	Typ
A	0.375	0.40	0.39
A1	0	0.05	0.02
A3	-	-	0.10
b	0.10	0.20	0.15
D	0.55	0.65	0.60
D1	0.35	0.45	0.40
E	0.75	0.85	0.80
E1	0.20	0.30	0.25
e	-	-	0.35
K	-	-	0.20
L	0.20	0.30	0.25
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	0.350
X	0.200
X1	0.450
X2	0.550
Y	0.375
Y1	0.475
Y2	1.000

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